

IN THE CLAIMS:

Please cancel Claims 55 to 65 without prejudice or disclaimer of the subject matter presented therein. The claims, as pending in the subject application, read as follows:

1 to 65. (Cancelled)

66. (Previously Presented) A fabrication method of a semiconductor device for use in a reflection type display apparatus having a reflective face, the fabrication method comprising the steps:

forming a first insulating film on a substrate on which at least one switching element is formed;

removing a portion of the first insulating film by an etching process to form a first concave section with the first insulating film being removed, the first concave section resulting in a wiring pattern and contact holes;

forming a film of an electroconductive metal material on the first insulating film and in the first concave section with the first insulating film being removed;

polishing the metal material film to remove the metal material formed on the first insulating film;

washing the surface of the substrate including an upper surface of the polished metal material film and an upper surface of the first insulating film which is exposed by the polishing;

forming a second insulating film which covers the metal material formed in the first concave section with the first insulating film being removed;

forming a second concave section with the second insulating film being removed;

forming a film of an electroconductive metal material on the second insulating film and in the second concave section with the second insulating film being removed;

polishing the metal material to remove the metal material formed on the second insulating film, thereby forming the reflective face; and

washing the surface of the substrate including the reflective face and an upper surface of the second insulating film which is exposed by the polishing,

wherein either of the washing steps comprises the steps of washing the surface of the substrate by means of an ultrasonic wave washing with a washing liquid to which an ultrasonic wave at a frequency band of not less than 800 kHz is applied, and subsequently washing the surface of the substrate by means of a scrubbing washing or a high-pressure jet washing.